



YEA SHIN TECHNOLOGY CO., LTD

BSS84

P-Channel Enhancement MOSFET

VDS= -50V, ID= -130mA

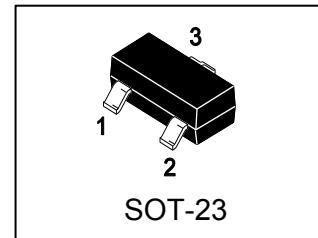


FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- Energy Efficient

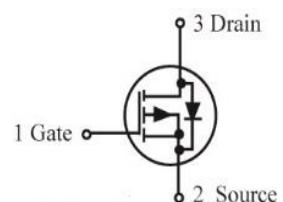
MARKING

PD



PACKAGE INFORMATION

Package	Shipping
SOT-23	3000/Tape&Reel



MAXIMUM RATINGS (TJ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	-50	V _{dc}
Gate-to-Source Voltage – Continuous	V _{GS}	± 20	V _{dc}
Drain Current – Continuous @ T _A = 25°C – Pulsed Drain Current (t _p ≤ 10 μs)	I _D I _{DM}	-130 -520	mA
Total Power Dissipation @ T _A = 25°C	P _D	225	mW
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C
Thermal Resistance – Junction-to-Ambient	R _{θJA}	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T _L	260	°C

DEVICE CHARACTERISTICS

BSS84

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage ($V_{GS} = 0 \text{ Vdc}$, $I_D = -250 \mu\text{Adc}$)	$V_{(\text{BR})\text{DSS}}$	-50	-	-	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = -25 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$) ($V_{DS} = -50 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$) ($V_{DS} = -50 \text{ Vdc}$, $V_{GS} = 0 \text{ Vdc}$, $T_J = 125^\circ\text{C}$)	I_{DSS}	-	-	-0.1 -15 -60	μAdc
Gate-Body Leakage Current ($V_{GS} = \pm 20 \text{ Vdc}$, $V_{DS} = 0 \text{ Vdc}$)	I_{GSS}	-	-	± 10	μAdc

ON CHARACTERISTICS (Note 1.)

Gate-Source Threaded Voltage ($V_{DS} = V_{GS}$, $I_D = -1.0 \text{ mAdc}$)	$V_{GS(\text{th})}$	-0.8	-	-2.0	Vdc
Static Drain-to-Source On-Resistance ($V_{GS} = -5.0 \text{ Vdc}$, $I_D = -100 \text{ mAdc}$)	$r_{DS(\text{on})}$	-	5.0	10	Ohms
Transfer Admittance ($V_{DS} = -25 \text{ Vdc}$, $I_D = 100 \text{ mAdc}$, $f = 1.0 \text{ kHz}$)	$ y_{fs} $	50	-	-	mS

DYNAMIC CHARACTERISTICS

Input Capacitance	($V_{DS} = -5.0 \text{ Vdc}$)	C_{iss}	-	30	-	pF
Output Capacitance	($V_{DS} = -5.0 \text{ Vdc}$)	C_{oss}	-	10	-	
Transfer Capacitance	($V_{DG} = -5.0 \text{ Vdc}$)	C_{rss}	-	5.0	-	

SWITCHING CHARACTERISTICS (Note 2.)

Turn-On Delay Time	($V_{DD} = -15 \text{ Vdc}$, $I_D = -2.5 \text{ Adc}$, $R_L = 50 \Omega$)	$t_{d(\text{on})}$	-	2.5	-	ns
Rise Time		t_r	-	1.0	-	
Turn-Off Delay Time		$t_{d(\text{off})}$	-	16	-	
Fall Time		t_f	-	8.0	-	

SOURCE-DRAIN DIODE CHARACTERISTICS

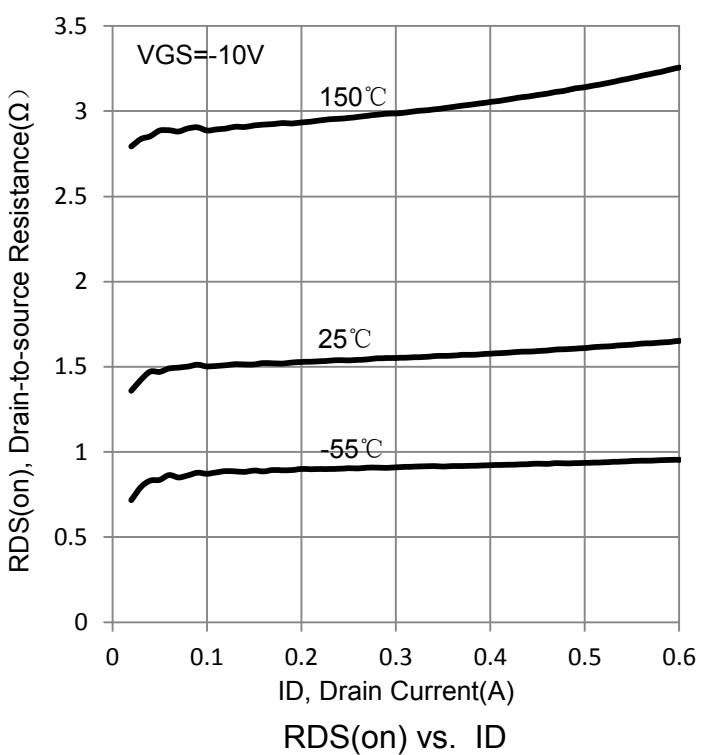
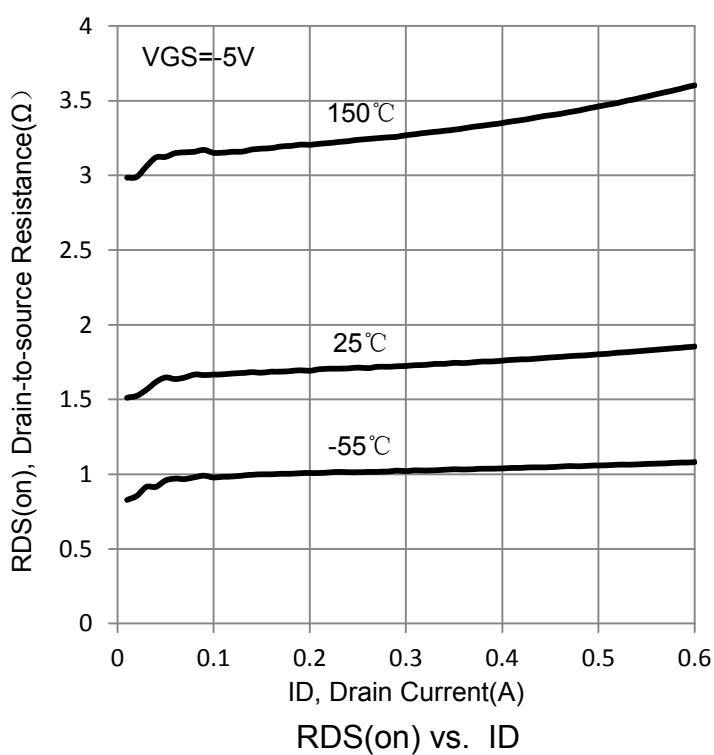
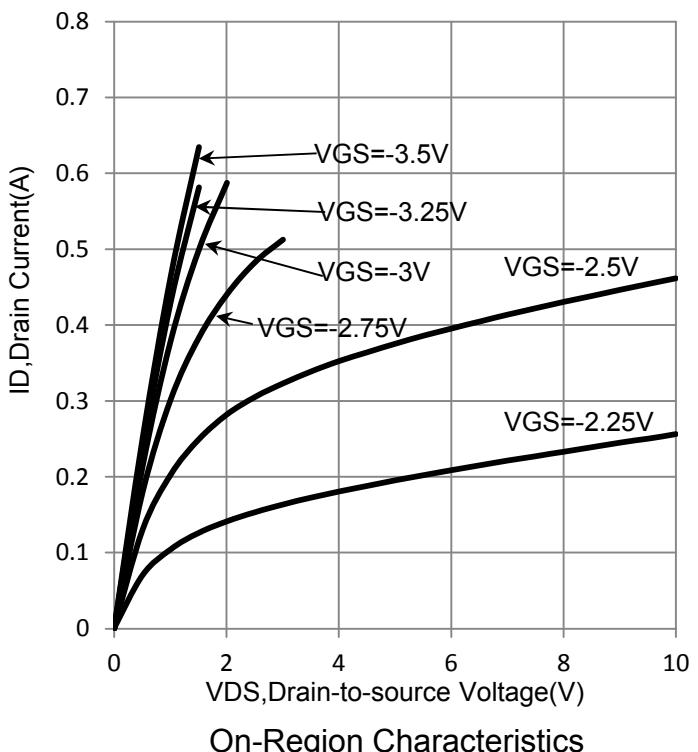
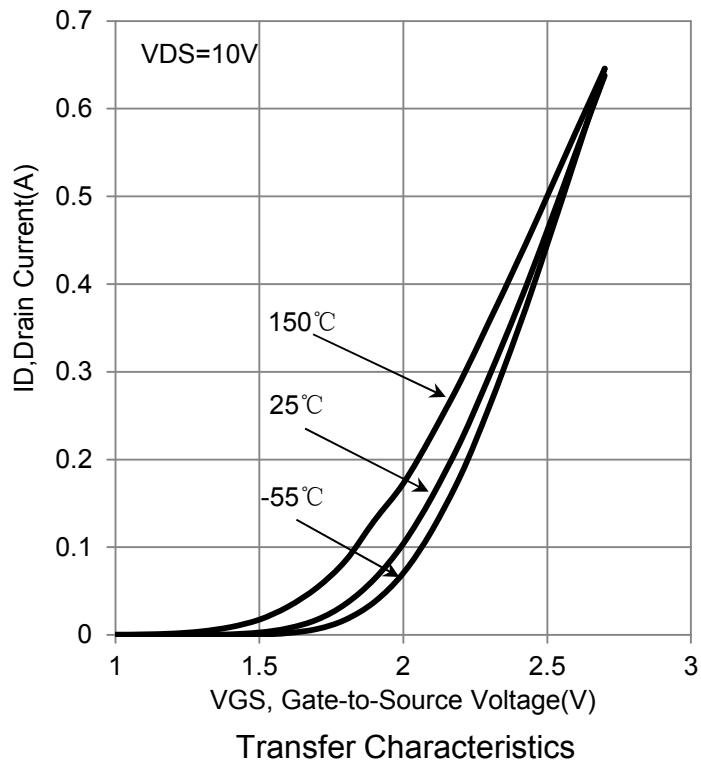
Continuous Current	I_S	-	-	-0.130	A
Pulsed Current	I_{SM}	-	-	-0.520	
Forward Voltage (Note 2.)	V_{SD}	-	-2.5	-	

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.
2. Switching characteristics are independent of operating junction temperature.

DEVICE CHARACTERISTICS

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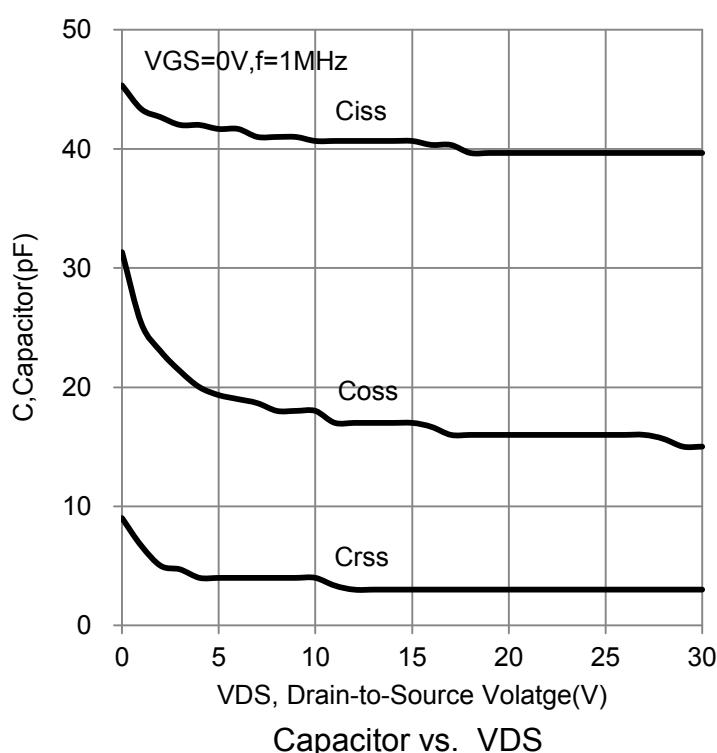
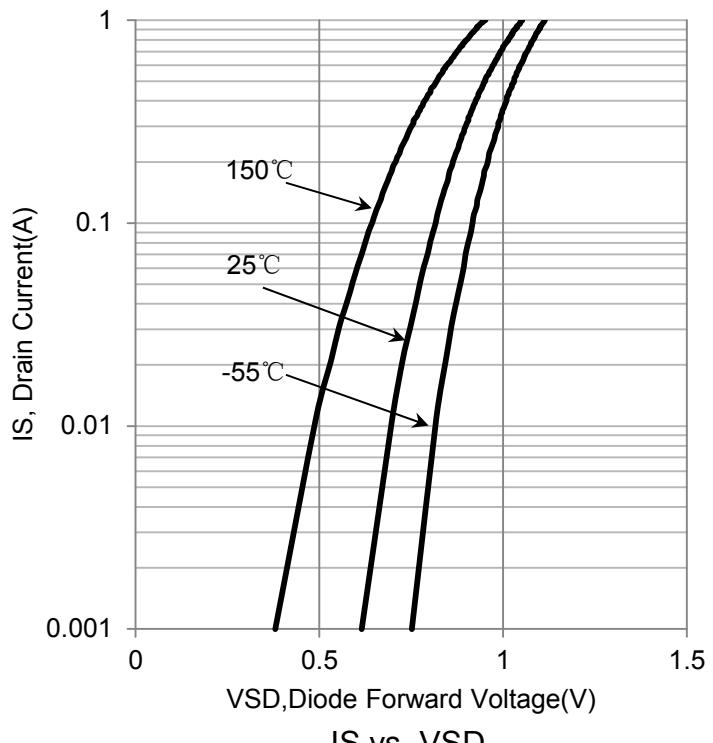
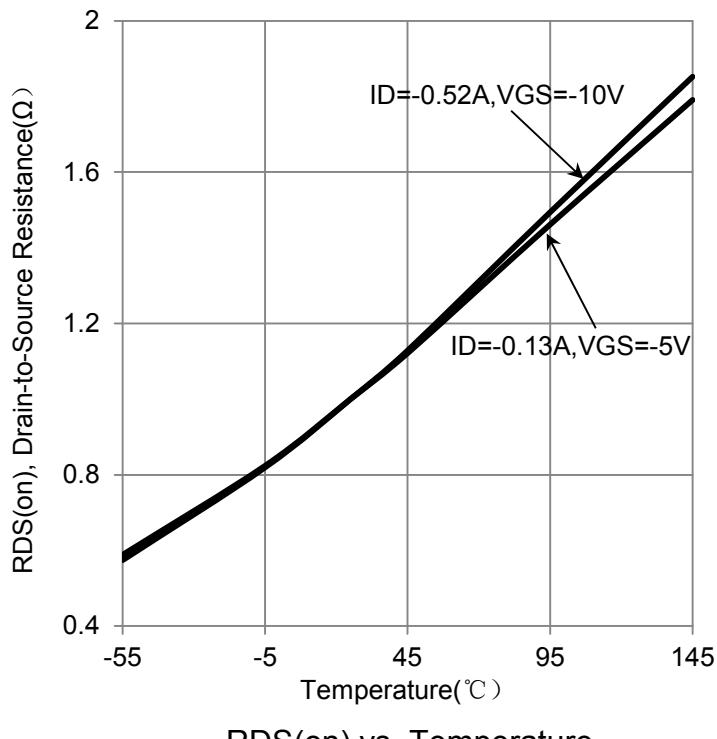
TYPICAL ELECTRICAL CHARACTERISTICS



DEVICE CHARACTERISTICS

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TYPICAL ELECTRICAL CHARACTERISTICS



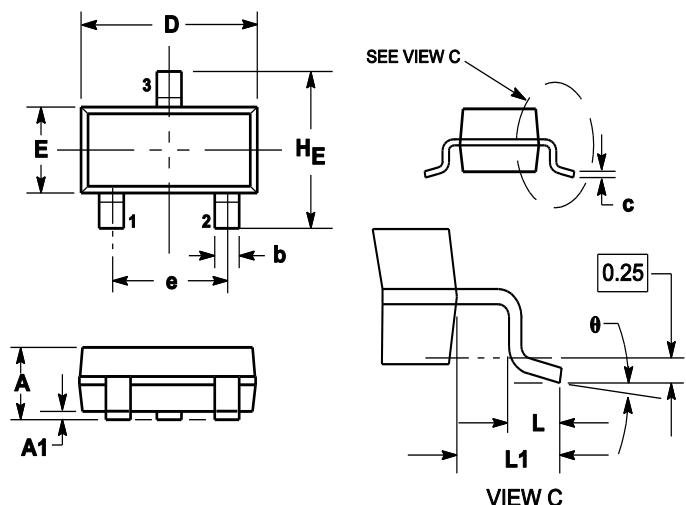
PACKAGE OUTLINE & DIMENSIONS

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OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

SOLDERING FOOTPRINT

